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	O I PHEORMATION DISCLOSURE CITATION				•	FUJI: 141A Applicant(s)		10/646,586		
1	(Use several sheets (f necessary)					Applicants) 'Katsunori UENO				
						Filing Date		Group Art Unit		
	MOV 2 0 2003 2			August 22, 2003		2811				
	U.S. PATENT DOCUMENTS									
1	EXAMINE INITIAL	REP	DOCUMENT NUMBER	DATE		NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
,	5	US	5,776,837	7/98	Palmour .		438	767	)	
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	· C.	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
	"Vital Issues for SiC Power Devices"; K. Hara; Materials Science Forum Vols. 264-268 (1998); pgs. 901-906; 1998 Trans Tech Publications, Switzerland									
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	EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.									